

DIGITRON SEMICONDUCTORS

2N1671A - C

UNI JUNCTION TRANSISTOR

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Base 1 – emitter reverse voltage	V_{B1E}	30	V
Base 2 – emitter reverse voltage	V_{B2E}	30	V
Interbase voltage	V_{B1B2}	35	V
RMS emitter current	I_{FRMS}	50	mA
Emitter peak current	I_{EM}	2	A
Total power dissipation	P_{tot}	450	mW
Maximum junction temperature	T_J	150	°C
Storage temperature range	T_{stg}	-55 to 150	°C

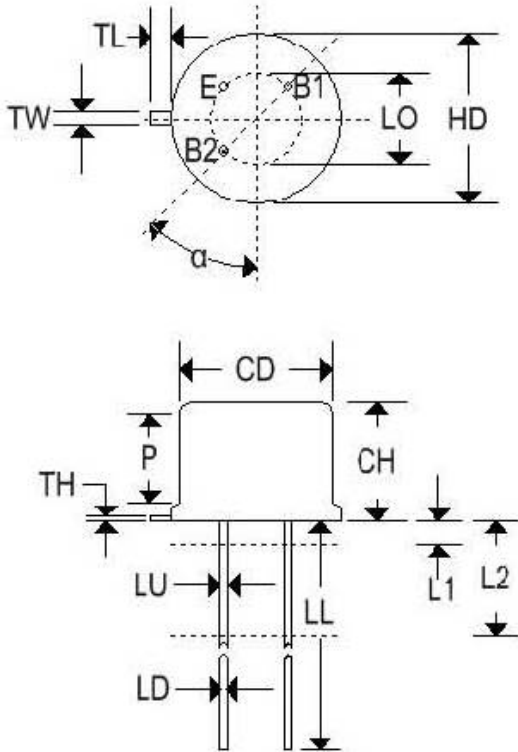
ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
Emitter reverse current	I_{EB20}	$V_{B2E} = 30\text{V}, I_{B1} = 0$	2N1671	-	-	-12	μA
			2N1671A	-	-	-12	
			2N1671B	-	-	-0.2	
Emitter saturation voltage	$V_{EB1(sat)}$	$V_{B2B1} = 10\text{V}, I_E = 50\text{mA}$	2N1671	-	-	5	V
			2N1671A	-	-	5	
			2N1671B	-	-	5	
Interbase resistance	R_{BBO}	$V_{B2B1} = 3\text{V}, I_E = 0$	2N1671	4.7	-	9.1	$\text{K}\square$
			2N1671A	4.7	-	9.1	
			2N1671B	4.7	-	9.1	
Intrinsic standoff ratio	η	$V_{B2B1} = 10\text{V}$	2N1671	0.47	-	0.62	-
			2N1671A	0.47	-	0.62	
			2N1671B	0.47	-	0.62	
Valley current	I_V	$V_{B2B1} = 10\text{V}, R_{B2} = 100\square$	2N1671	-	-	8	mA
			2N1671A	-	-	8	
			2N1671B	-	-	8	
Peak current	I_P	$V_{B2B1} = 25\text{V}$	2N1671	-	-	25	μA
			2N1671A	-	-	25	
			2N1671B	-	-	6	

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Dim	TO-5			
	Inches		Millimeters	
	Min	Max	Min	Max
HD	0.335	0.370	8.510	9.400
CD	0.305	0.335	7.750	8.510
CH	0.240	0.260	6.100	6.600
LL	1.500	-	38.100	-
LD	0.016	0.021	0.410	0.530
LU	0.016	0.019	0.410	0.480
P	0.100	-	2.540	-
TL	0.029	0.045	0.740	1.140
TW	0.028	0.034	0.710	0.860
TH	0.009	0.125	0.230	3.180
LO	0.141 NOM		3.590 NOM	
α	45°TP		45°TP	

Available Non-RoHS (standard) or RoHS compliant (add PBF suffix).

Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.